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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Chen et al.

Serial No.: 09/748,256

Group Art Unit: 2811

Filed: December 27, 2000

Examiner: Ori Nadav

For: METHOD FOR FABRICATING COMPLEMENTARY METAL OXIDE
SEMICONDUCTOR (CMOS) DEVICES ON A MIXED BULK AND SILICON-ON-
INSULATOR (SOI) SUBSTRATE

Honorable Assistant Commissioner of Patents
Washington, D.C. 20231

AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action dated August 14, 2001, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claim 40 without prejudice or disclaimer.

Please amend the claims to read as follows:

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29. (Amended) A semiconductor device comprising:
a bulk silicon region comprising single crystal silicon; and
a silicon-on-insulator (SOI) region comprising:
an insulator layer which is formed beneath an upper portion of said single
crystal silicon and has at least one lateral end portion adjacent to a lower portion of said
single crystal silicon; and
at least one isolation oxide formed in said upper portion of said single crystal
silicon so as to form at least one island of said single crystal silicon on an upper surface of
said insulator layer.

30. (Amended) The semiconductor device according to claim 29, wherein said at least